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ABSTRACT

0033 A method for using an isotropic wet etching process chemical process for trimming semiconductor feature sizes with improved critical dimension control including providing a hard mask overlying a substrate included in a semiconductor wafer said hard mask patterned for masking a portion of the substrate for forming a semiconductor feature according to an anisotropic plasma etching process; isotropically wet etching the hard mask to reduce a dimension of the hard mask prior to carrying out the anisotropic plasma etching process; and, anisotropically plasma etching a portion of the substrate not covered by the hard mask to form the semiconductor feature.